

NCE N-Channel Enhancement Mode Power MOSFET

Description

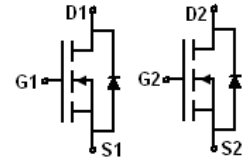
The NCE30D0808J uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch and PWM applications.

General Features

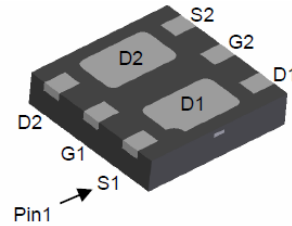
- $V_{DS} = 30V, I_D = 7.7A$
- $R_{DS(ON)} < 25m\Omega @ V_{GS}=10V$
- $R_{DS(ON)} < 35m\Omega @ V_{GS}=4.5V$
- High Power and current handling capability
- Lead free product is acquired
- Surface mount package

Application

- General Purpose Interfacing Switch
- Power Management Functions



Schematic diagram



DFNWB2X2-6L Bottom View

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
0808	NCE30D0808J	DFNWB2X2-6L	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	7.7	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	31	A
Maximum Power Dissipation	P_D	2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	62.5	$^\circ C/W$
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Electrical Characteristics ($T_C=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.5	3	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=7A$	-	22	25	m Ω
		$V_{GS}=4.5V, I_D=5A$	-	28	34	m Ω
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0MHz$	-	558	-	PF
Output Capacitance	C_{oss}		-	72.7	-	PF
Reverse Transfer Capacitance	C_{rss}		-	62.6	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	2.4	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	9	-	nS
Turn-Off Fall Time	t_f		-	2.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5A,$ $V_{GS}=10V$	-	12	-	nC
Gate-Source Charge	Q_{gs}		-	1.7	-	nC
Gate-Drain Charge	Q_{gd}		-	3.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=7.7A$	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	7.7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

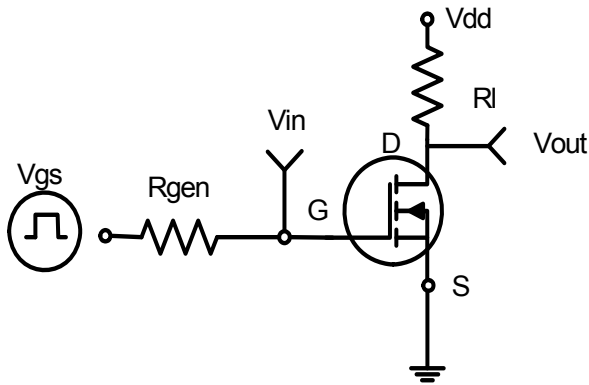


Figure 1: Switching Test Circuit

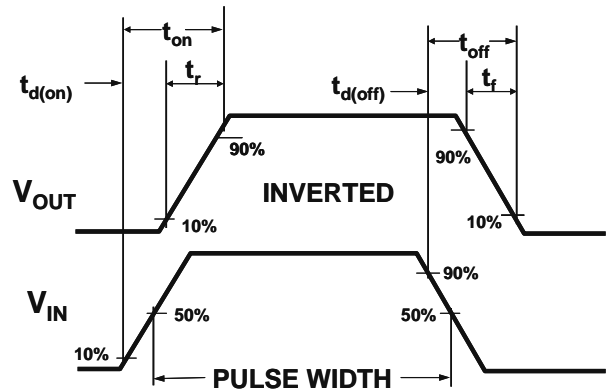


Figure 2: Switching Waveforms

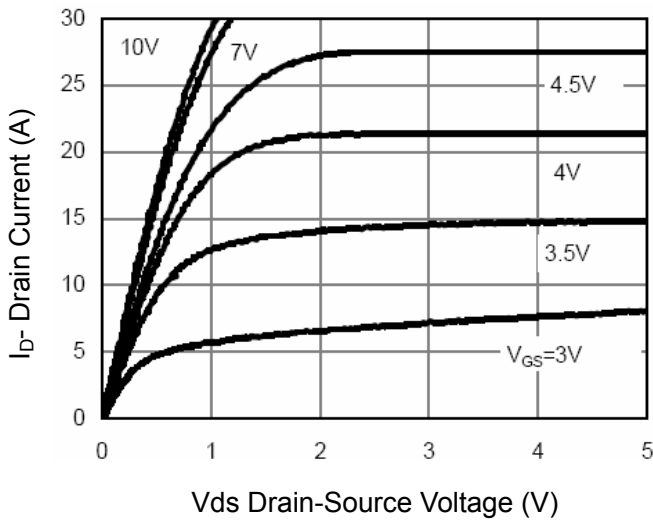


Figure 3 Output Characteristics

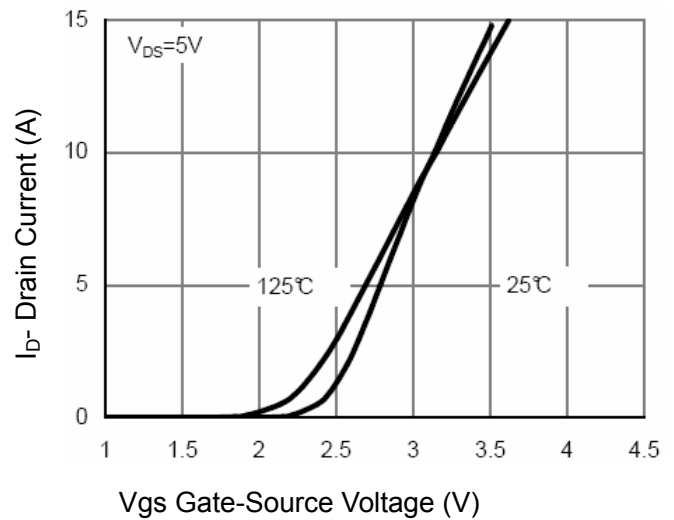


Figure 4 Transfer Characteristics

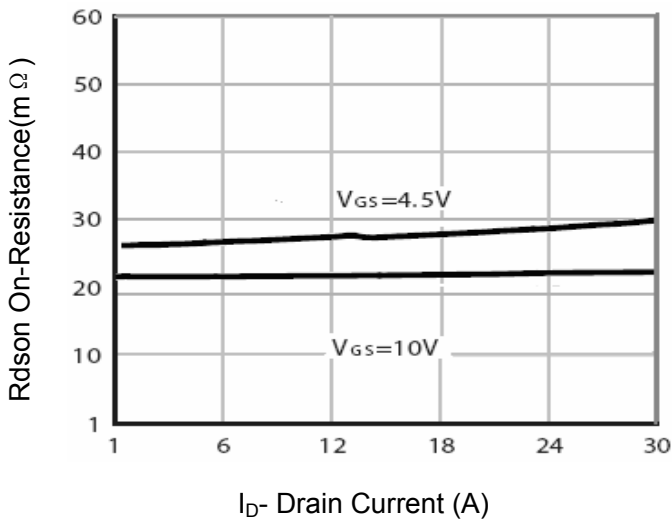


Figure 5 Drain-Source On-Resistance

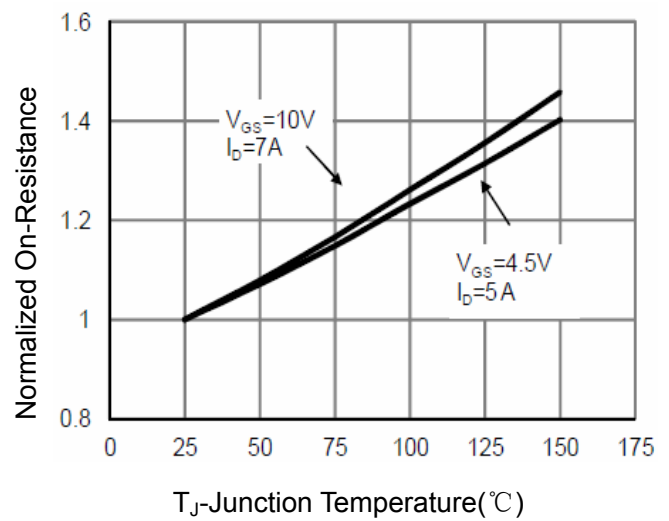
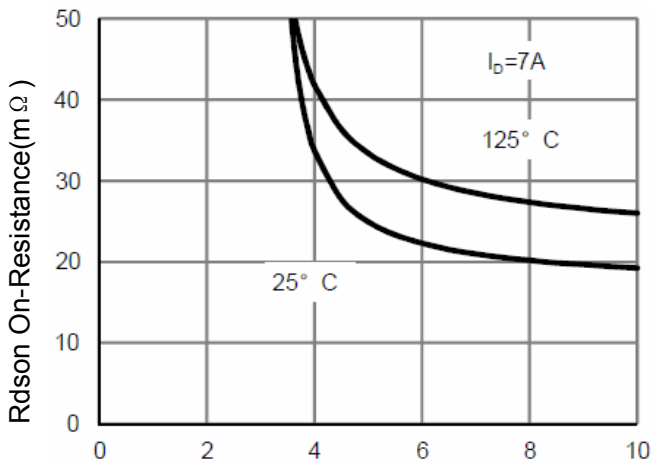
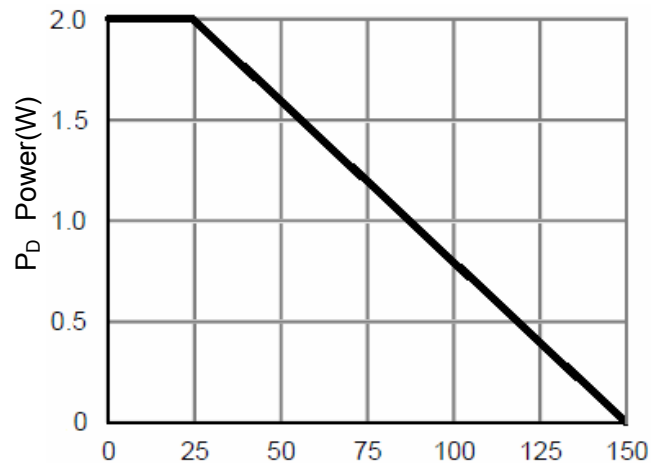


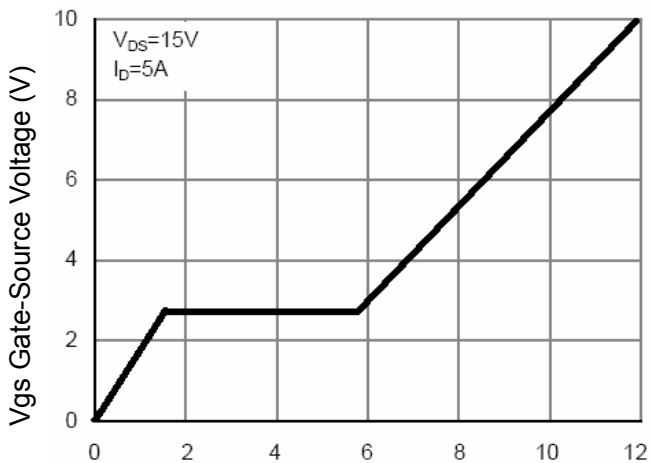
Figure 6 Drain-Source On-Resistance



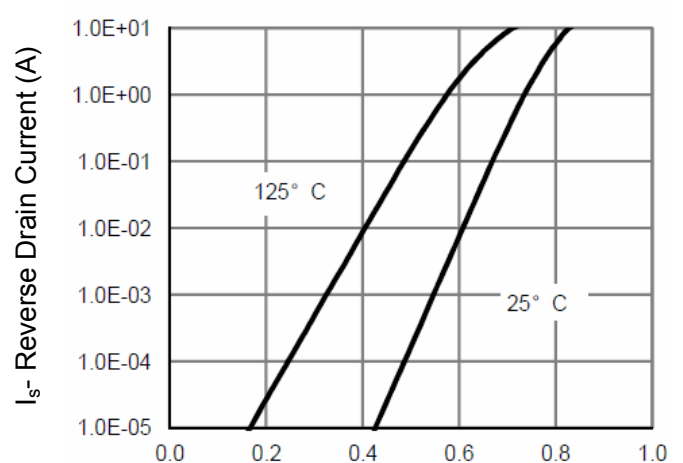
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



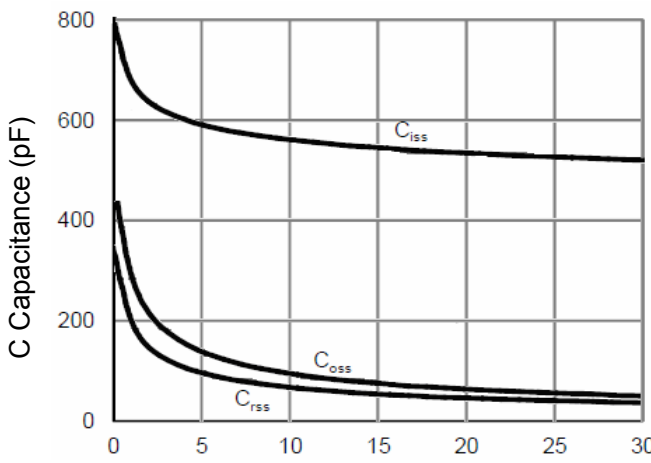
T_J-Junction Temperature (°C)
Figure 8 Power Dissipation



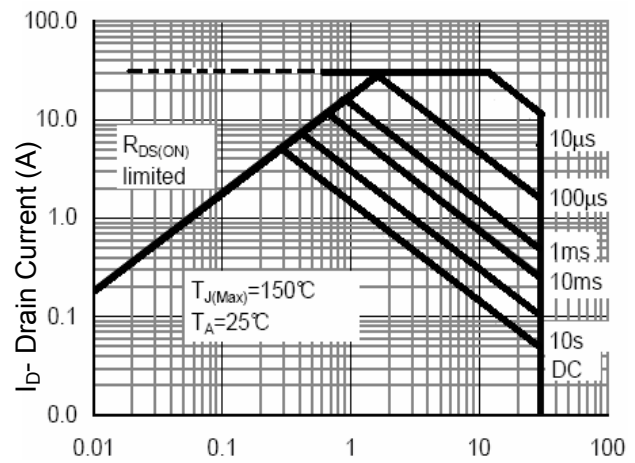
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vds Drain-Source Voltage (V)
Figure 10 Source-Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

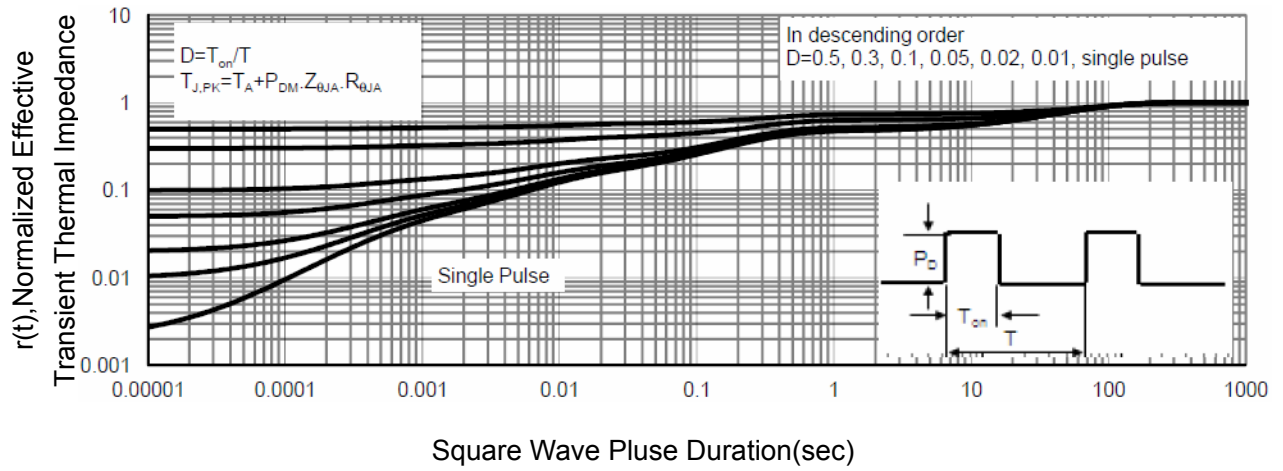
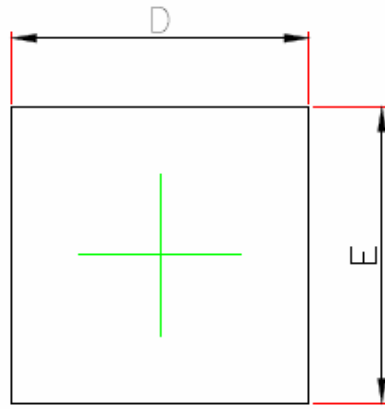
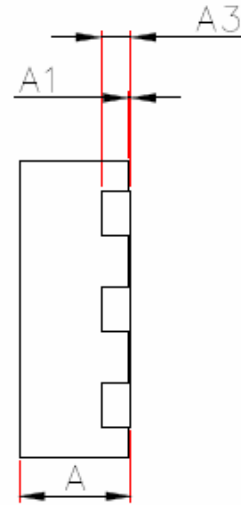


Figure 13 Normalized Maximum Transient Thermal Impedance

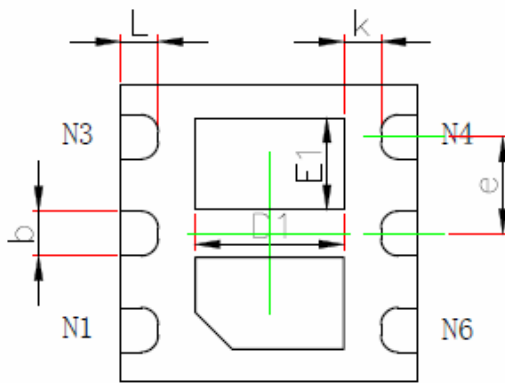
DFNWB2X2-6L Package Information



TOP VIEW



SIDE VIEW



BOTTOM VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.900	1.100	0.035	0.043
E1	0.520	0.720	0.020	0.028
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
k	0.200MIN.		0.008MIN.	
L	0.200	0.300	0.008	0.012

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